

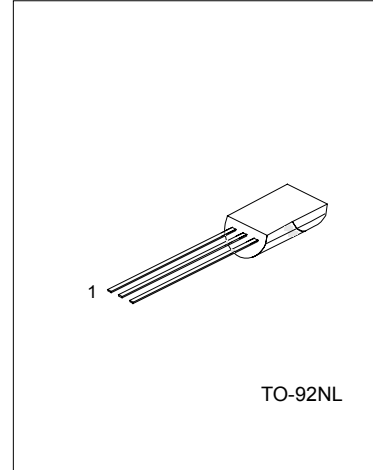
UTC2SD468

NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

FEATURES

- *Low frequency power amplifier
- *Complement to 2SB562



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	VCBO	25	V
Collector-Emitter Voltage	VCEO	20	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	Ic	1	A
Collector Peak Current	Ic(peak)	1.5	A
Collector Power Dissipation	PC	0.9	W
Junction Temperature	Tj	150	°C
Storage Temperature	TSTG	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to base breakdown voltage	V(BR)CBO	Ic=10μA, IE=0	25			V
Collector to emitter breakdown voltage	V(BR)CEO	Ic=1mA, RE=∞	20			V
Emitter to base breakdown voltage	V(BR)EBO	IE=10μA, Ic=0	5			V
Collector Cut-Off Current	ICBO	VCB=20V, IE=0			1	μA
DC Current transfer ratio	hFE	VCE=2V, Ic=0.5A (note)	85		240	
Collector to emitter saturation voltage	VCE(sat)	Ic=0.8A, IB=0.08A (note)		0.2	0.5	V
Base to emitter voltage	VBE	VCE=2V, Ic=0.5A (note)		0.79	1	V
Gain bandwidth product	fT	VCE=2V, Ic=0.5A (note)		190		MHz
Collector output capacitance	Cob	VCB=10V, IE=0, f=1MHz		22		pF

Note: Pulse test

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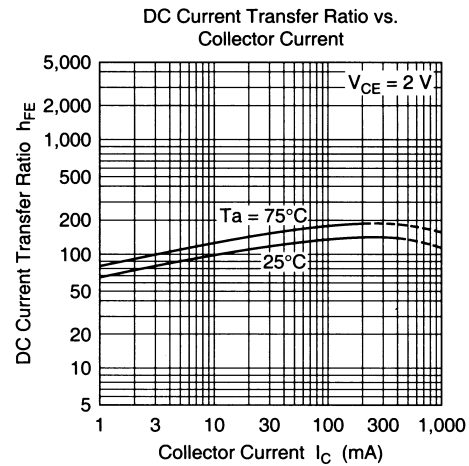
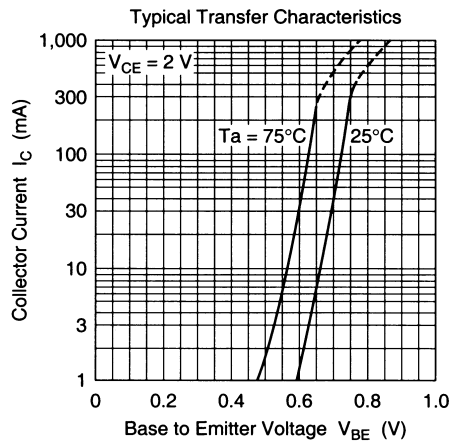
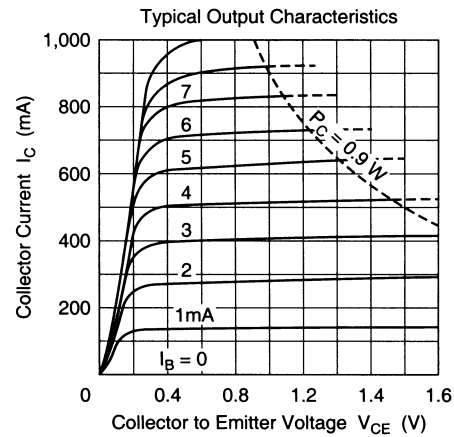
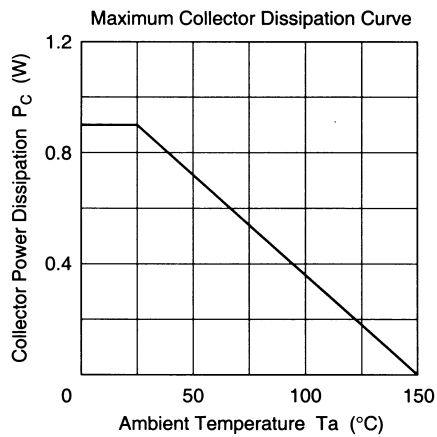
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QW-R211-003,A

CLASSIFICATION OF h_{FE}

RANK	B	C
RANGE	85 - 170	120 - 240

TYPICAL PERFORMANCE CHARACTERISTICS



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